SEMICONDUCTOR SUBSTRATE FOR LASER SEPARATION AND PROCESS FOR MANUFACTURING THREE-DIMENSIONAL SEMICONDUCTOR STRUCTURES

ABSTRACT

A semiconductor substrate (Sub) designed to allow laser separation of an active material layer (ActMat), comprising: a support substrate (Sprt); an inorganic layer (Inorg) on the support substrate, the inorganic layer being formed from a material chosen from Al2O3, TiO2, WO3, La2O3, LaAlO3 and TiN; an electrically insulating layer (Ins) on the inorganic layer; and the active material layer (ActMat) on the electrically insulating layer, the active material layer being single-crystal.

Figure to be published with the abstract: Fig. 3